



### Product Description

The S8740240P is a Hybrid Push Pull amplifier module. The part employs GaAs die and is operated from 40MHz to 870MHz. It provides excellent linearity and superior return loss performance with low noise and optimal reliability.

### Features

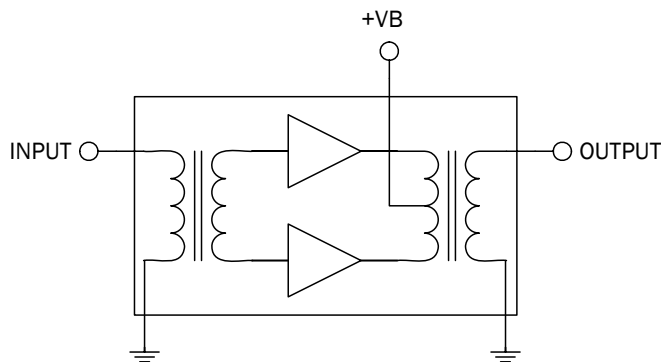
- Excellent Linearity
- Superior Return Loss Performance
- Extremely Low Distortion
- Optimal Reliability
- Low Noise
- Unconditionally Stable Under All Terminations
- 23.5dB Min. Gain at 870MHz
- 255 mA Max. at 24VDC

### Applications

- 40 MHz to 870 MHz CATV Amplifier Systems

#### Optimum Technology Matching® Applied

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- RF MEMS



Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall</b>					$V_B = 24V; T_{MB} = 30^\circ C; Z_S = Z_L = 75\Omega$
Power Gain*	22.5	23.0	23.5	dB	f=50 MHz
	23.5	24.0	25.0	dB	f=870 MHz
Slope [1]	0.5	1.0	2.0	dB	f=40 MHz to 870 MHz
Flatness of Frequency Response			±0.5	dB	f=40 MHz to 870 MHz
Input Return Loss	20.0			dB	f=40 MHz to 160 MHz
	18.0			dB	f=160 MHz to 870 MHz
Output Return Loss	20.0			dB	f=40 MHz to 160 MHz
	18.0			dB	f=160 MHz to 870 MHz
Noise Figure		2.5	3.5	dB	f=50 MHz to 870 MHz
Total Current Consumption (DC)		250.0	255.0	mA	
<b>Distortion data 40MHz to 870MHz</b>					
CTB		-66	-64	dBc	132 ch flat; $V_0 = 40 \text{ dBmV}^{[2]}$
XMOD		-59	-57	dBc	132 ch flat; $V_0 = 40 \text{ dBmV}^{[2]}$
CSO		-66	-64	dBc	132 ch flat; $V_0 = 40 \text{ dBmV}^{[2]}$

1. The slope is defined as the difference between the gain at the start frequency and the gain at the stop frequency.  
 2. 132 channels, NTSC frequency raster: 55.25 MHz to 865.25 MHz, +40dBmV flat output level.  
 Composite Second Order (CSO) - The CSO parameter (both sum and difference products) is defined by the NCTA.  
 Composite Triple Beat (CTB) - The CTB parameter is defined by the NCTA.  
 Cross Modulation (XMOD) - Cross modulation (XMOD) is measured at baseband (selective voltmeter method), referenced to 100% modulation of the carrier being tested.

## Absolute Maximum Ratings

Parameter	Rating	Unit
RF Input Voltage (single tone)	75	dBmV
DC Supply Over-Voltage (5 minutes)	30	V
Storage Temperature	-40 to +100	°C
Operating Mounting Base Temperature	-30 to +100	°C

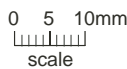
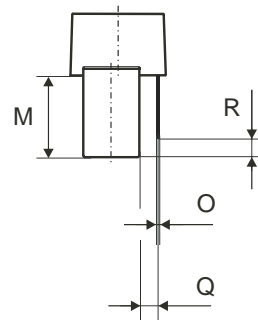
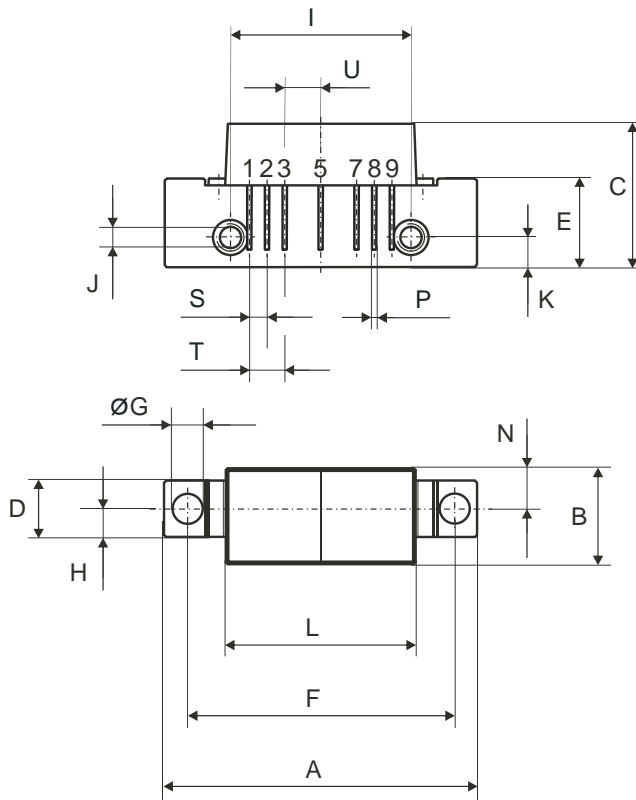


**Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

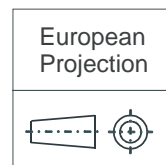
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### Pinning:

Pin	1	2	3	4	5	6	7	8	9
Function	INPUT	GND	GND	+VB	GND	GND	GND	OUTPUT	

### Notes:



### All Dimensions in mm:

	nominal	min	max
A	44,6 ± 0,2	44,4	44,8
B	13,6 ± 0,2	13,4	13,8
C	20,4 ± 0,5	19,9	20,9
D	8 ± 0,15	7,85	8,15
E	12,6 ± 0,15	12,45	12,75
F	38,1 ± 0,2	37,9	38,3
G	4 +0,2 / -0,05	3,95	4,2
H	4 ± 0,2	3,8	4,2
I	25,4 ± 0,2	25,2	25,6
J	UNC 6-32	-	-
K	4,2 ± 0,2	4,0	4,4
L	27,2 ± 0,2	27,0	27,4
M	11,6 ± 0,5	11,1	12,1
N	5,8 ± 0,4	5,4	6,2
O	0,25 ± 0,02	0,23	0,27
P	0,45 ± 0,03	0,42	0,48
Q	2,54 ± 0,3	2,24	2,84
R	2,54 ± 0,5	2,04	3,04
S	2,54 ± 0,25	2,29	2,79
T	5,08 ± 0,25	4,83	5,33
U	5,08 ± 0,25	4,83	5,33